

[illegible]

A cross-sectional view of a semiconductor device. A substrate (10) is shown with a trench (9) formed in its surface. A gate structure (13) is formed on the trench walls and bottom. The gate structure (13) consists of a gate oxide layer (13a) and a gate conductive layer (13b). A gate electrode (5) is formed on the gate conductive layer (13b). A source/drain region (6) is formed in the substrate (10) adjacent to the gate structure (13). A contact layer (2) is formed on the source/drain region (6). A contact pad (3) is formed on the contact layer (2). A wiring (8) is connected to the contact pad (3) and extends to a terminal (12). A window (W) is formed in the substrate (10) adjacent to the trench (9).

10

1

2

3

4

5

6

7

8

9

11

13a

13b

14

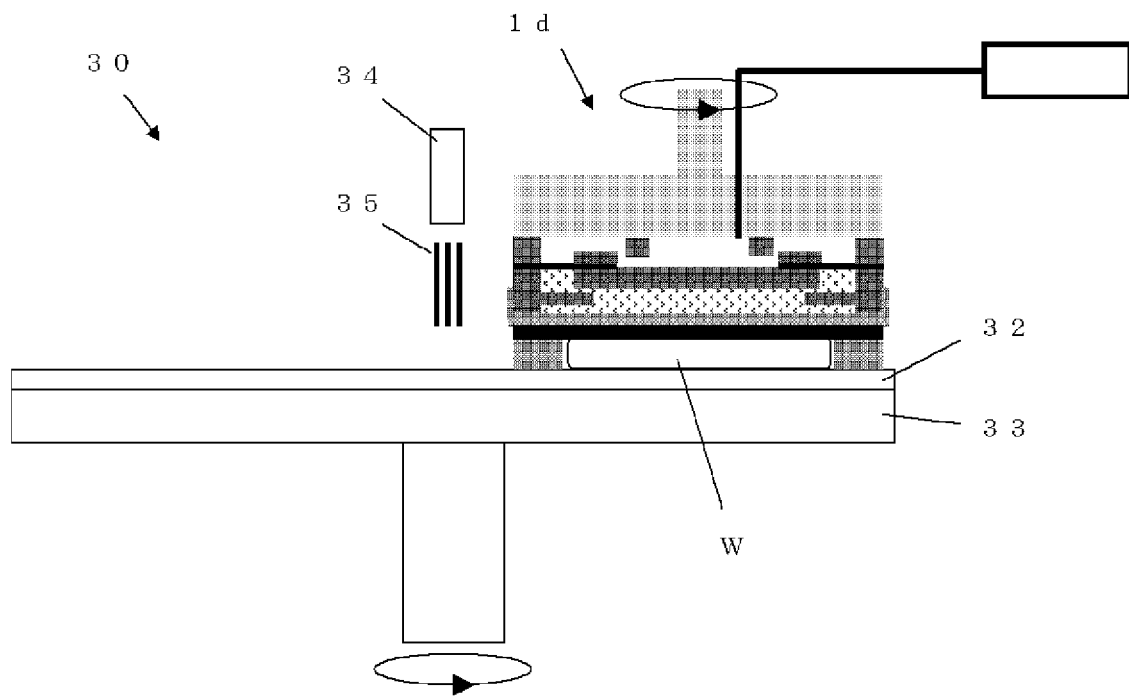
1d

12

W

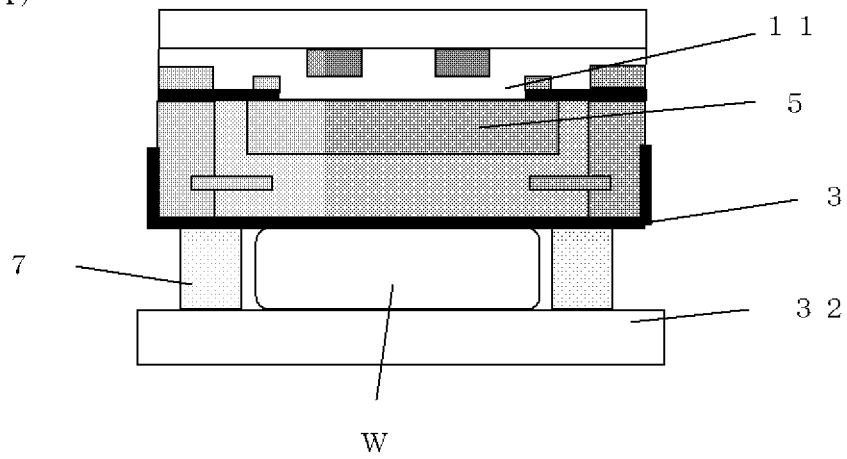
[illegible]

[図7]

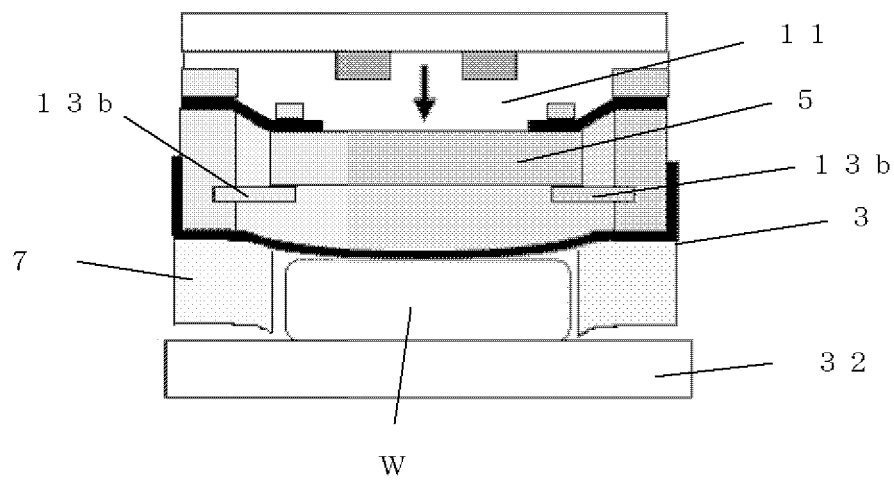


[図8]

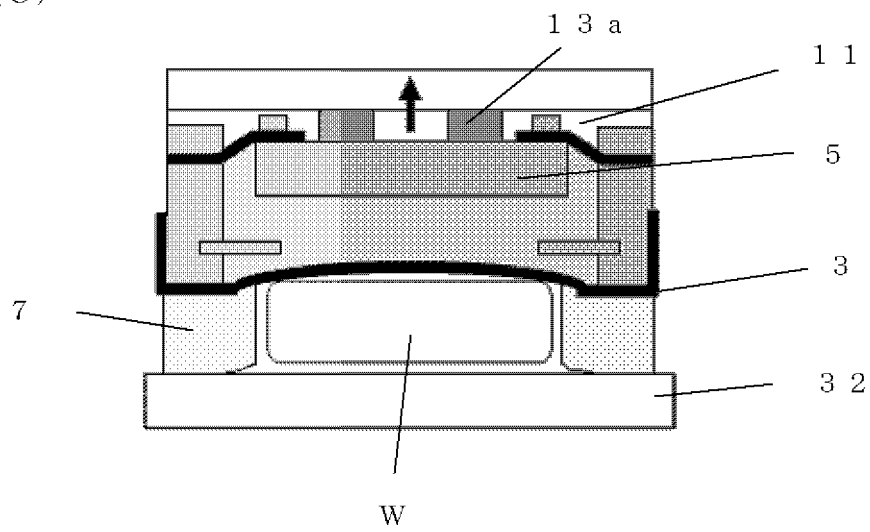
(A)



(B)

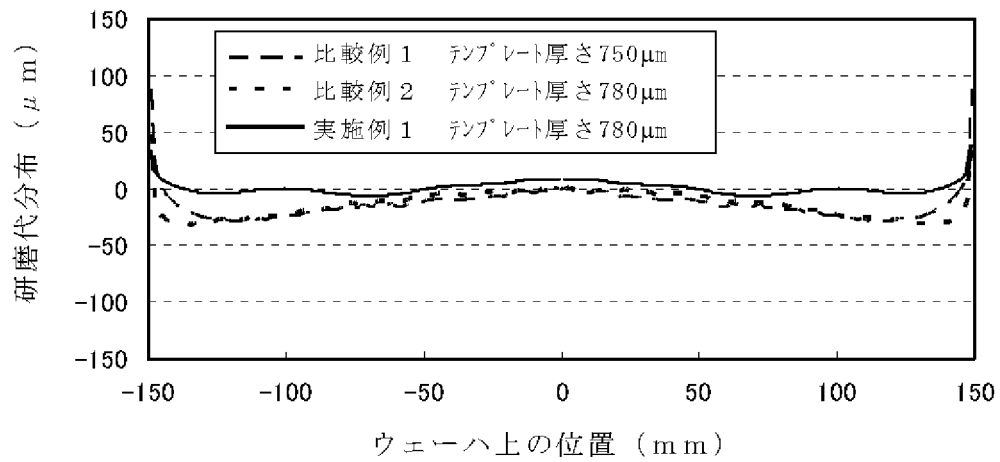


(C)

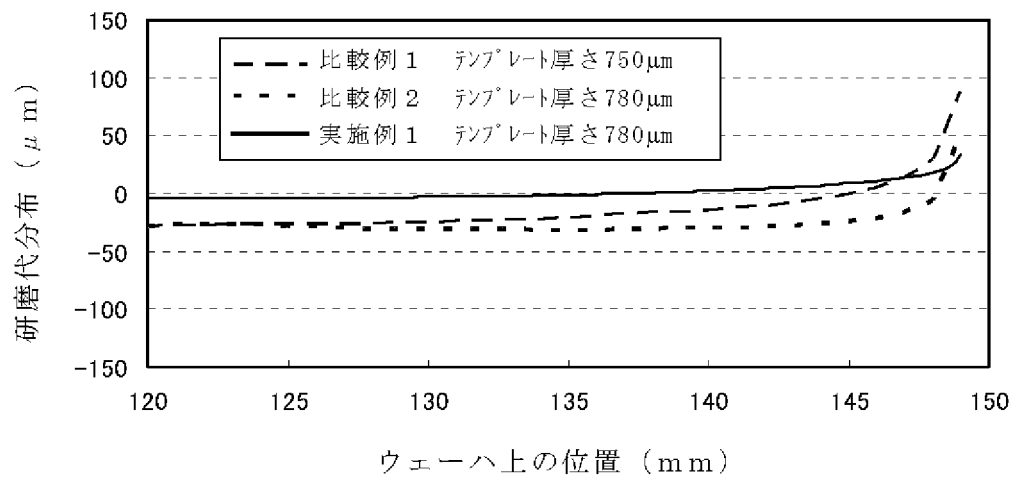


[図9]

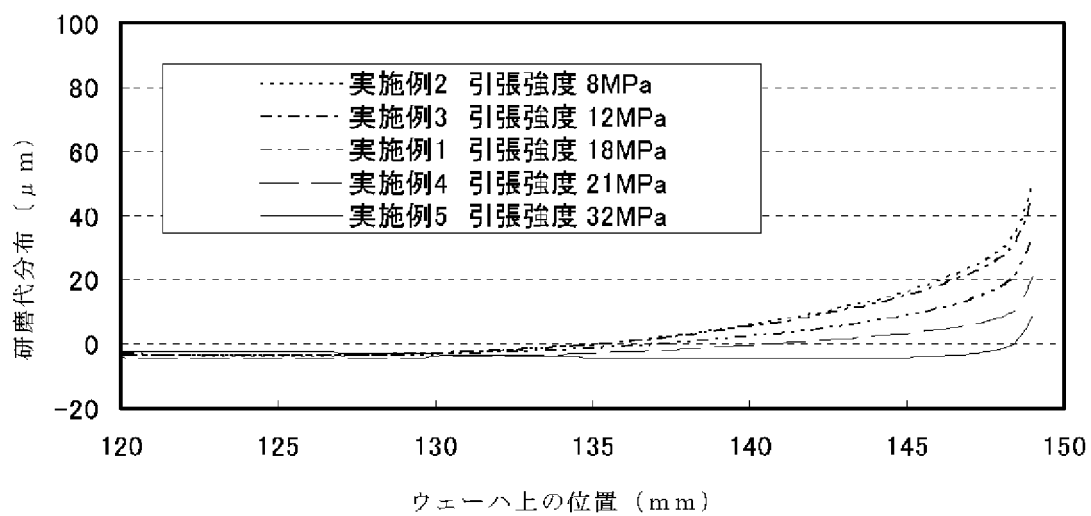
(A)



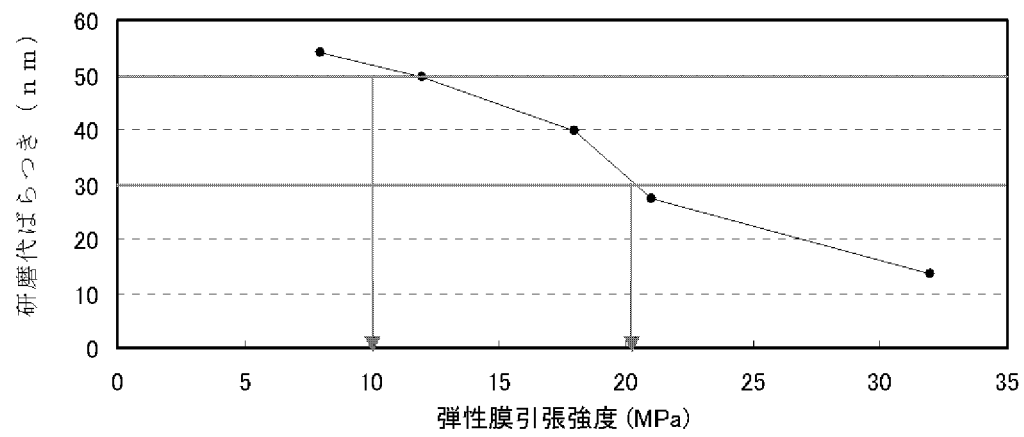
(B)



[図10]

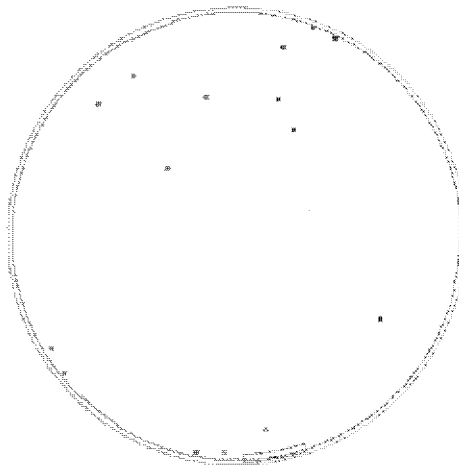


[図11]



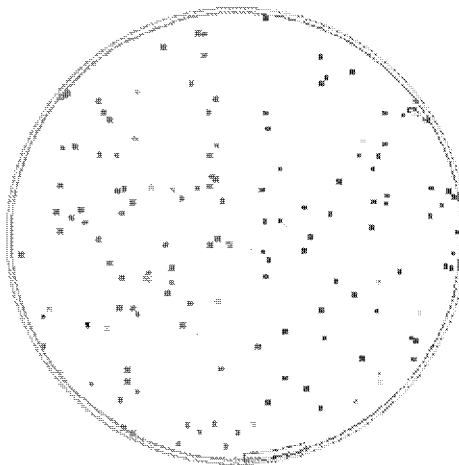
[図12]

(A)



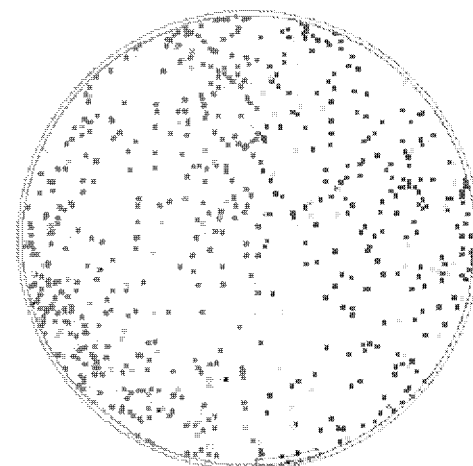
欠陥数 18個

(B)



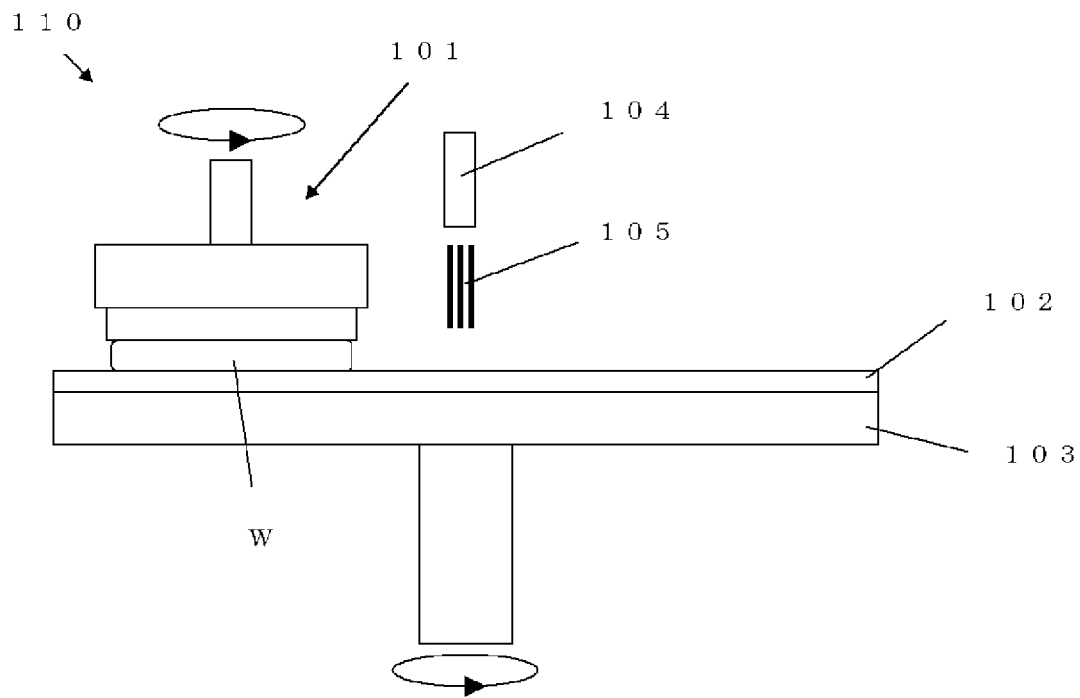
欠陥数 216個

(C)

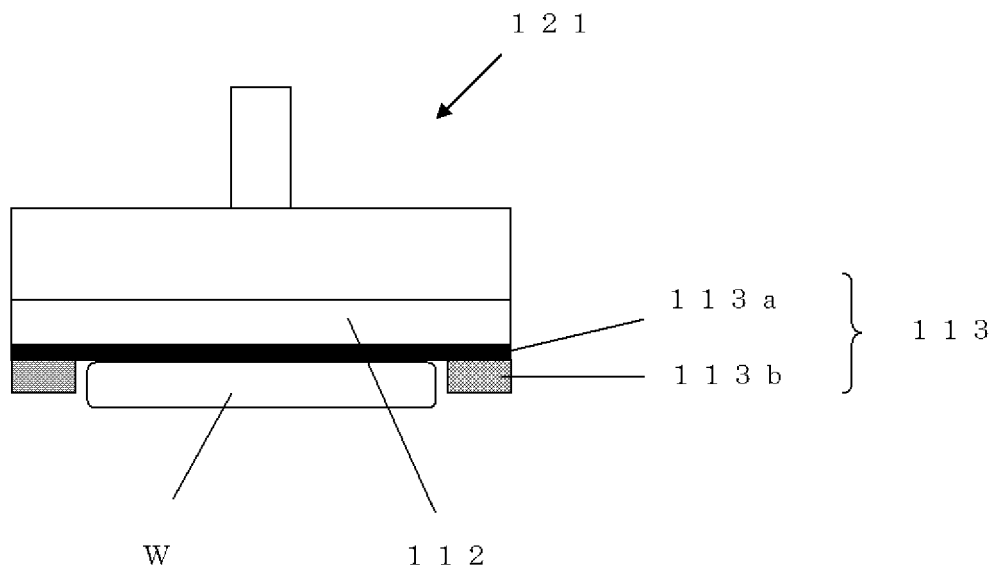


欠陥数 684個

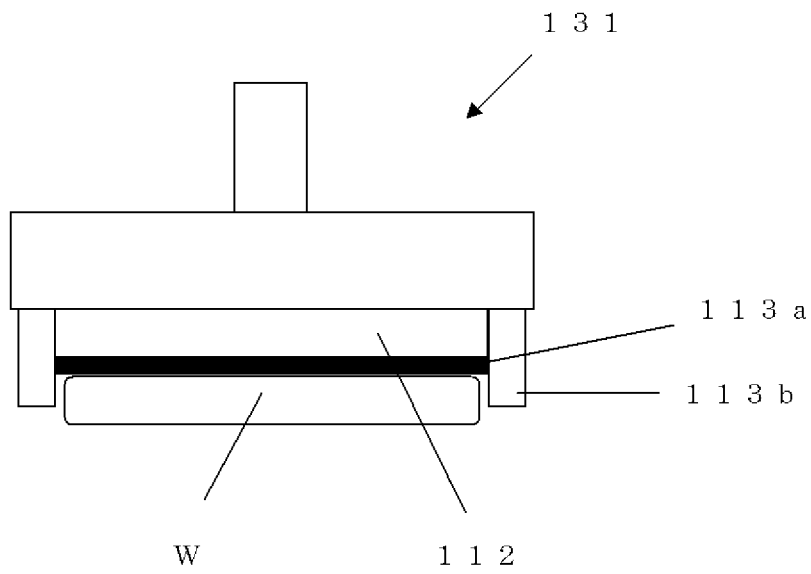
[図13]



[図14]



[図15]



[図16]

